The ZMS035N08HB combines advanced trench MOSFET technology with a low resistance package to provide

T_C =25

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}$TC=25	140	A
	$I_{D@}$TC=75	106.4	A
	$I_{D@}$TC=100	88.2	A
Pulsed Drain Current	I_{DM}	320	A
Total Power Dissipation(TC=25)	P_D@TC=25	150	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	125	mJ
Avalanche Current@L=0.1mH	I_{AS}	50	A

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.75	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	2		4	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=80V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V ,V_{DS} =0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A				
Forward Transconductance	g_{FS}	V_{DS} =10V, I_D=40A				
Source-drain voltage	V_{SD}	Is=30A				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	3100	-	pF

Fig.1 Gate-Charge Characteristics

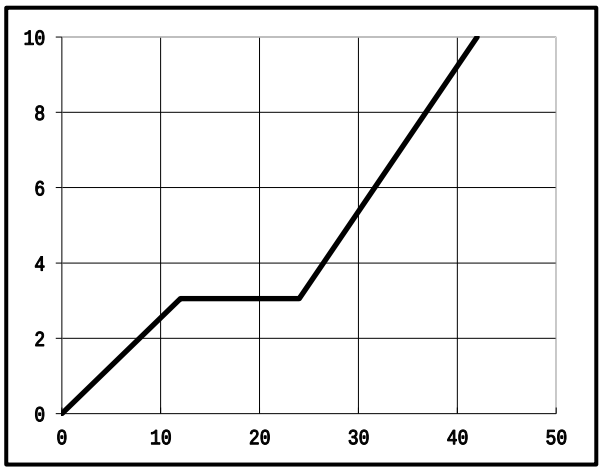

Fig.2 Capacitance Characteristics

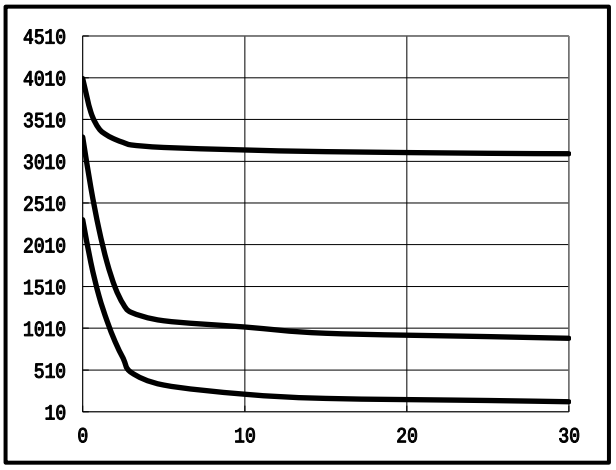

Fig.3 Power Dissipation

Fig.4 Typical output Characteristics

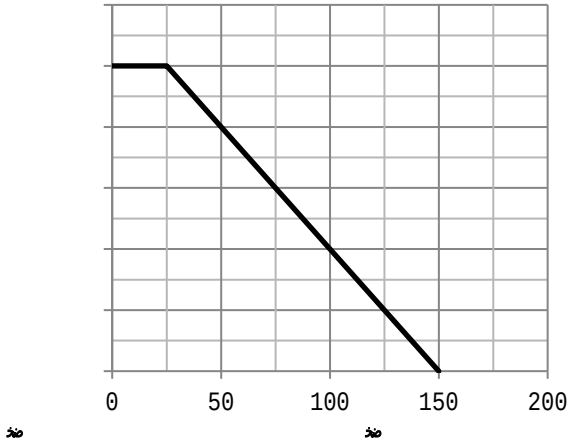

Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current

Fig.7 On-Resistance VS Gate Source Voltage

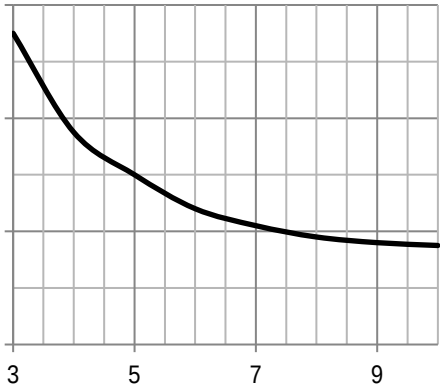

Fig.8 On-Resistance V.S Junction Temperature

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform

Dimensions (TO-263)

Unit mm